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SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

CSD18534Q5A-MS

Product specification

Description

The CSD18534Q5A-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

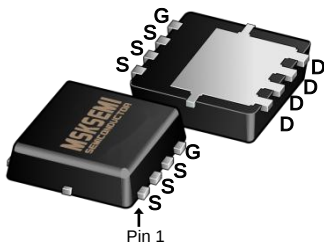
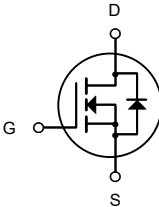
Features

- $V_{DS} = 60V$ $I_D = 65A$
- $R_{DS(ON)} < 11m\Omega$ $V_{GS} = 10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

DFN5X6-8L	N-Channel MOSFET	Marking
		

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	65	A
$I_D @ T_c = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	49	A
I_{DM}	Pulsed Drain Current ²	180	A
EAS	Single Pulse Avalanche Energy ³	56	mJ
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	89	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$

Electrical Characteristics($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =20A	-	8	11	mΩ
		V _{GS} =4.5V, I _D =10A	-	14	20	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	930	-	pF
C _{oss}	Output Capacitance		-	370	-	pF
C _{rss}	Reverse Transfer Capacitance		-	20	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	-	19	-	nC
Q _{gs}	Gate-Source Charge		-	4.8	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	4.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =20A, R _G =1.6Ω, V _{GS} =10V	-	4.9	-	ns
t _r	Turn-on Rise Time		-	31	-	ns
t _{d(off)}	Turn-off Delay Time		-	23	-	ns
t _f	Turn-off Fall Time		-	8.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	65	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	240	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.4	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25°C, I _F =20A, dI/dt=100A/μs	-	34	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	14	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, R_G=25\Omega, L=0.5mH, I_{AS}=12A$
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure1: Output Characteristics

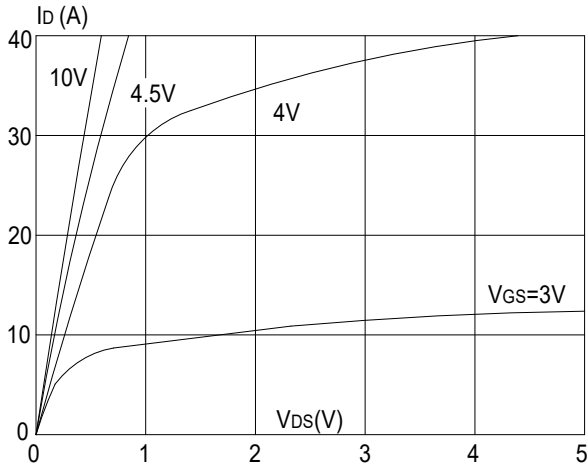


Figure 2: Typical Transfer Characteristics

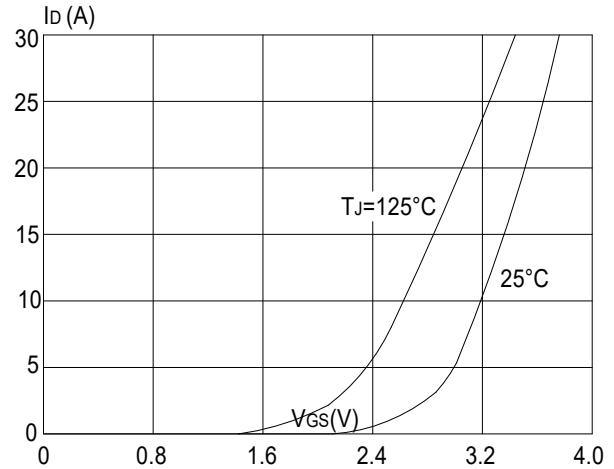


Figure 3: On-resistance vs. Drain Current

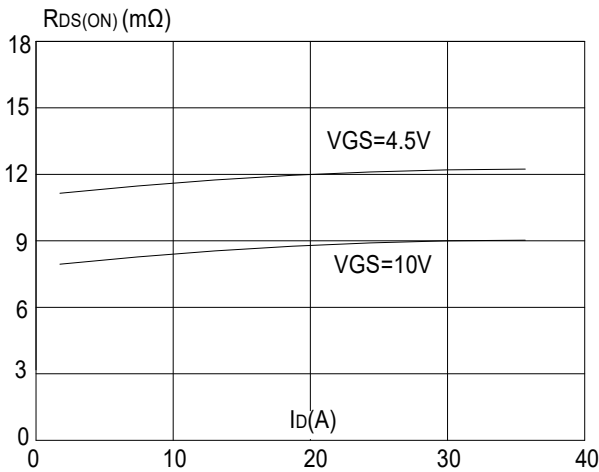


Figure 4: Body Diode Characteristics

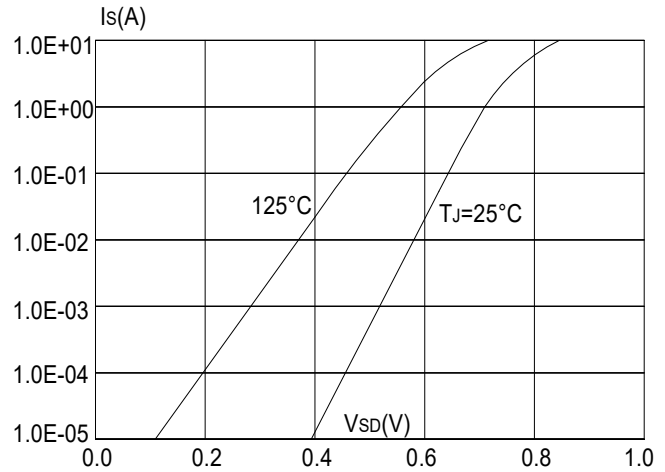


Figure 5: Gate Charge Characteristics

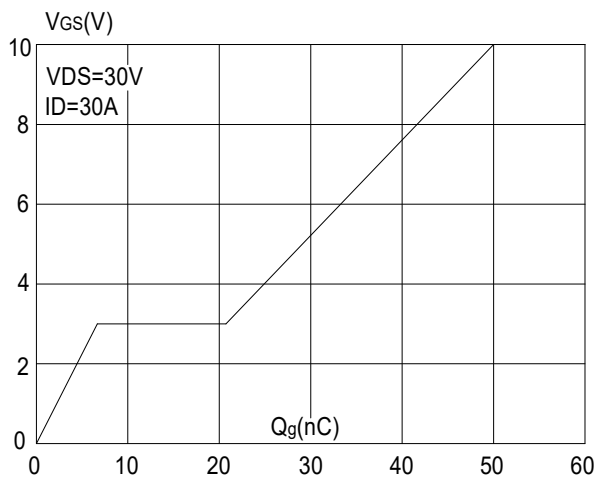


Figure 6: Capacitance Characteristics

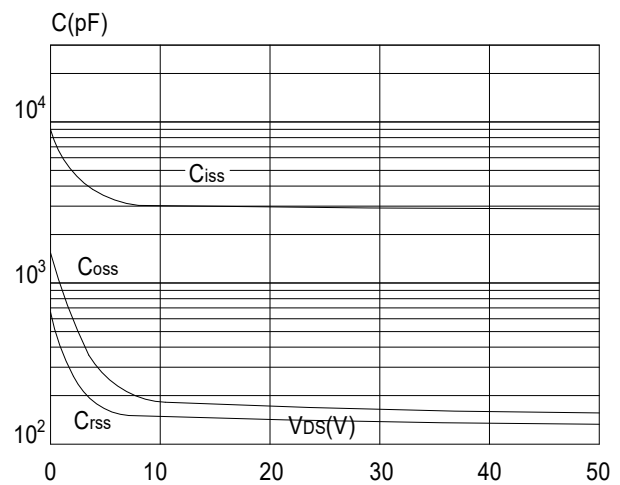


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

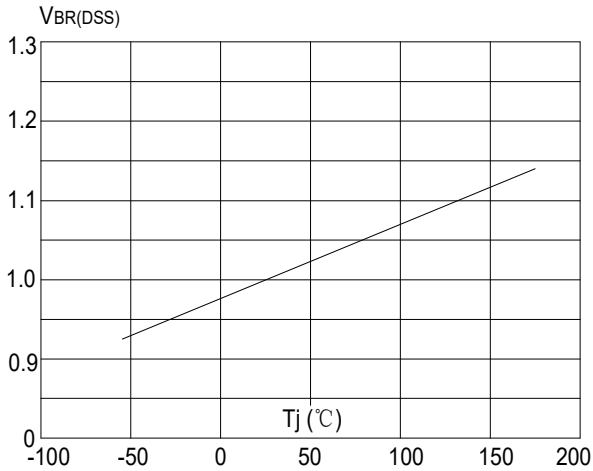


Figure 8: Normalized on Resistance vs. Junction Temperature

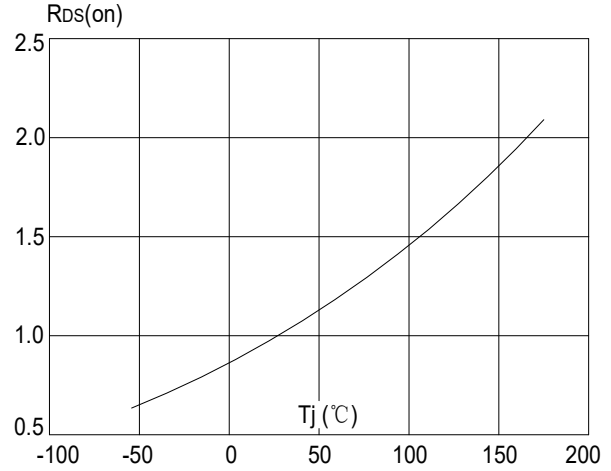


Figure 9: Maximum Safe Operating Area

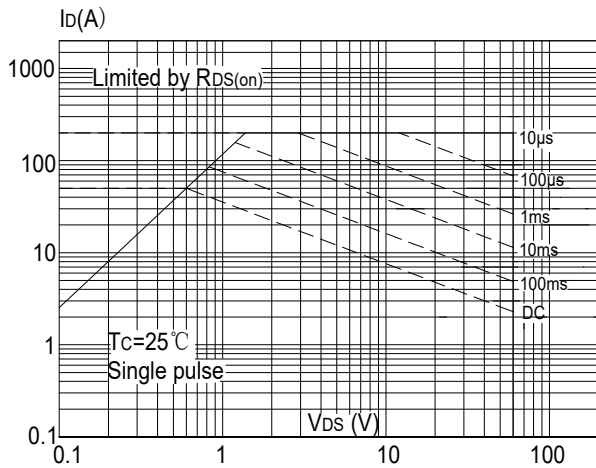


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

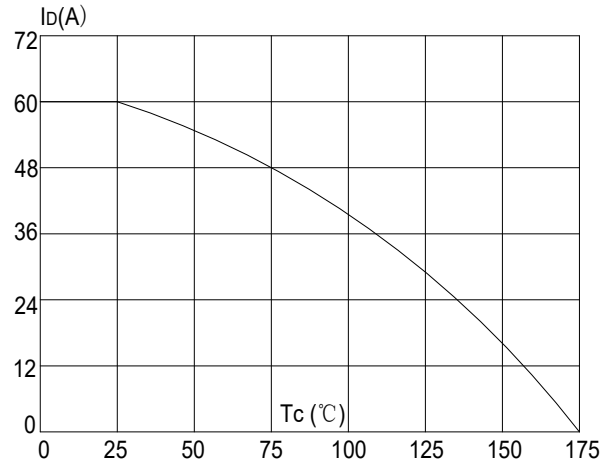
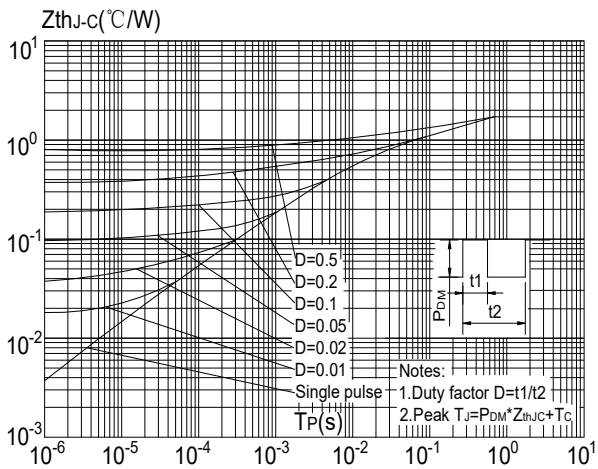
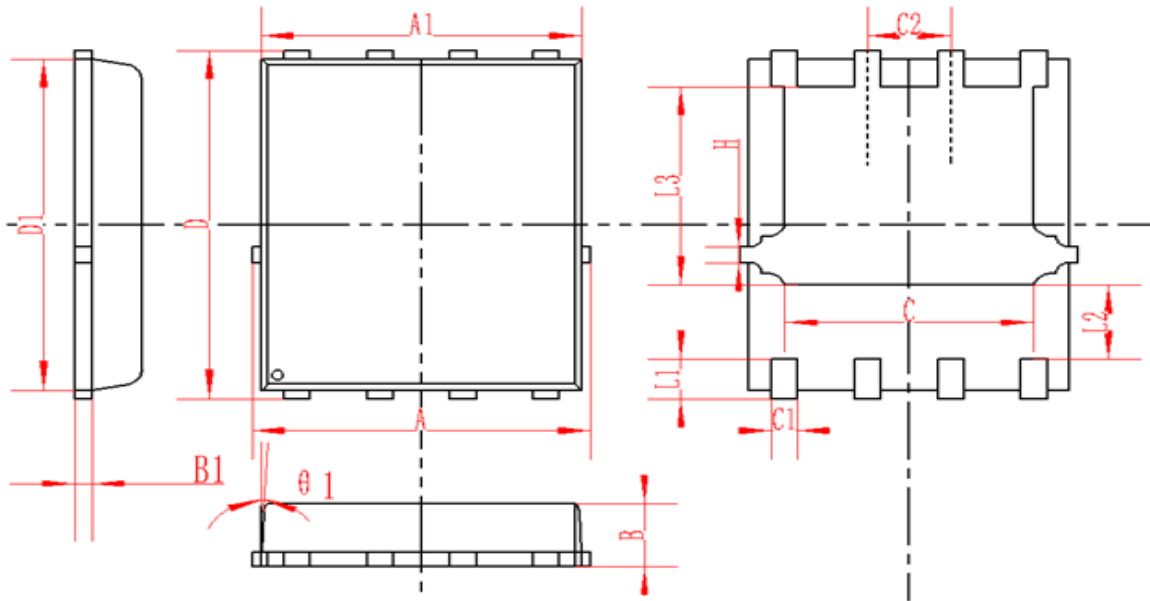


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



DFN5X6-8L Package Information


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
$\theta 1$	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

REEL SPECIFICATION

P/N	PKG	QTY
CSD18534Q5A-MS	DFN5X6-8L	5000

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